**Product data sheet** 

## 1. General description

Dual ultrafast power diodes in a SOT78 (TO-220AB) plastic package.

#### 2. Features and benefits

- · Fast switching
- High thermal cycling performance
- Low forward voltage drop
- Low switching loss
- Low thermal resistance
- Soft recovery characteristic

## 3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- · Output rectifiers in high-frequency switched-mode power supplies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	500	V
I <sub>O(AV)</sub>	average output current	SQW; $\delta$ = 0.5; T <sub>mb</sub> $\leq$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	-	-	20	Α
Static characte	eristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.87	1.05	V
Dynamic chara	acteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}; \underline{\text{Fig. 5}}$	-	50	60	ns





**Dual ultrafast power diodes** 

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	A1
2	K	cathode	<b>├</b> ○ ┤	K K
3	A2	anode 2	1 2 3 TO-220AB (SOT78)	sym125

# 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV34-500	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

**Dual ultrafast power diodes** 

#### **Limiting values 7**.

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	500	V
$V_{RWM}$	crest working reverse voltage		-	500	V
V <sub>R</sub>	reverse voltage	T <sub>mb</sub> ≤ 138 °C; DC	-	500	V
I <sub>O(AV)</sub>	average output current	SQW; $\delta$ = 0.5; T <sub>mb</sub> $\leq$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	-	20	А
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 115 °C; per diode	-	20	А
I <sub>FSM</sub>	non-repetitive peak forward current	SIN; $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; per diode	-	120	А
		SIN; $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode	-	132	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

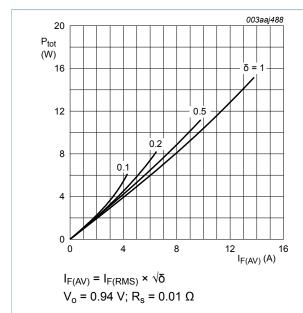


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

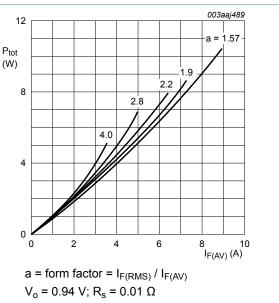


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

**Dual ultrafast power diodes** 

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 3	-	-	2.4	K/W
	mounting base	with heatsink compound; both diodes conducting	-	-	1.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

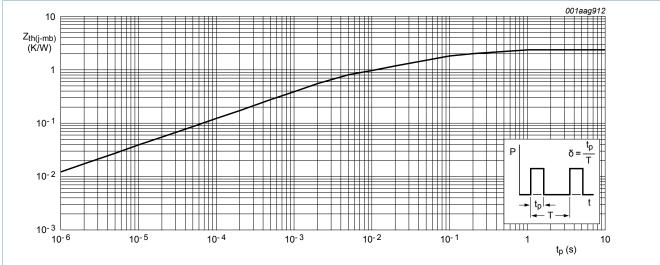


Fig. 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

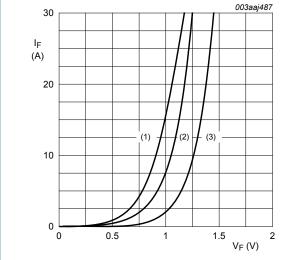
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#### **Dual ultrafast power diodes**

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.1	1.35	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.87	1.05	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 500 V; T <sub>j</sub> = 25 °C	-	10	50	μΑ
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic cl	haracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 5}}; \underline{\text{Fig. 6}}$	-	50	60	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}; \underline{\text{Fig. 5}}$	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; \underline{\text{Fig. 8}}; \underline{\text{Fig. 5}}$	-	4	5	A
$V_{FRM}$	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 10 \text{ A}/\mu\text{s}; T_j = 25 °C;$ Fig. 9	-	2.5	-	V



 $V_0 = 0.94 \text{ V}; R_s = 0.01 \Omega$ 

(1) T<sub>i</sub> = 150 °C; typical values

(2) T<sub>j</sub> = 150 °C; maximum values

(3) T<sub>j</sub> = 25 °C; maximum values

Fig. 4. Forward current as a function of forward voltage; per diode

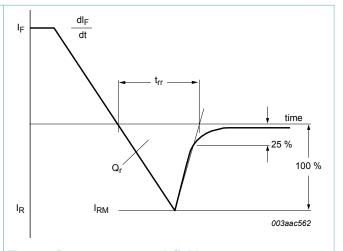
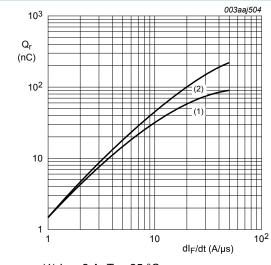


Fig. 5. Reverse recovery definitions; ramp recovery

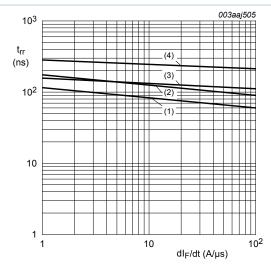
#### **Dual ultrafast power diodes**



(1) 
$$I_F = 2 A$$
;  $T_j = 25 °C$ 

(2) 
$$I_F = 20 \text{ A}$$
;  $T_j = 25 \,^{\circ}\text{C}$ 

Fig. 6. Recovered charge as a function of rate of change of forward current; per diode; maximum values



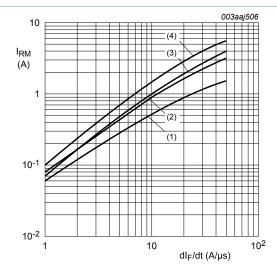
(1) 
$$I_F = 1 A$$
;  $T_j = 25 °C$ 

(2) 
$$I_F = 1 A$$
;  $T_j = 100 °C$ 

(3) 
$$I_F$$
 = 20 A;  $T_j$  = 25 °C

(4) 
$$I_F = 20 \text{ A}$$
;  $T_j = 100 \,^{\circ}\text{C}$ 

Fig. 7. Reverse recovery time as a function of rate of change of forward current; per diode; maximum values



(1) 
$$I_F = 1 A$$
;  $T_j = 25 °C$ 

(2) 
$$I_F = 1 A$$
;  $T_i = 100 \, ^{\circ}C$ 

(3) 
$$I_F = 20 \text{ A}$$
;  $T_i = 25 \,^{\circ}\text{C}$ 

(4) 
$$I_F = 20 \text{ A}$$
;  $T_j = 100 \,^{\circ}\text{C}$ 

Fig. 8. Peak reverse recovery current as a function of rate of change of forward current; per diode; maximum values

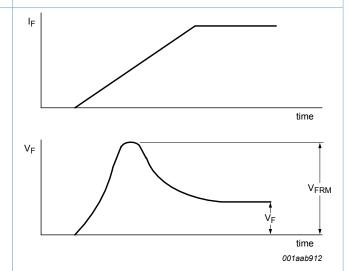
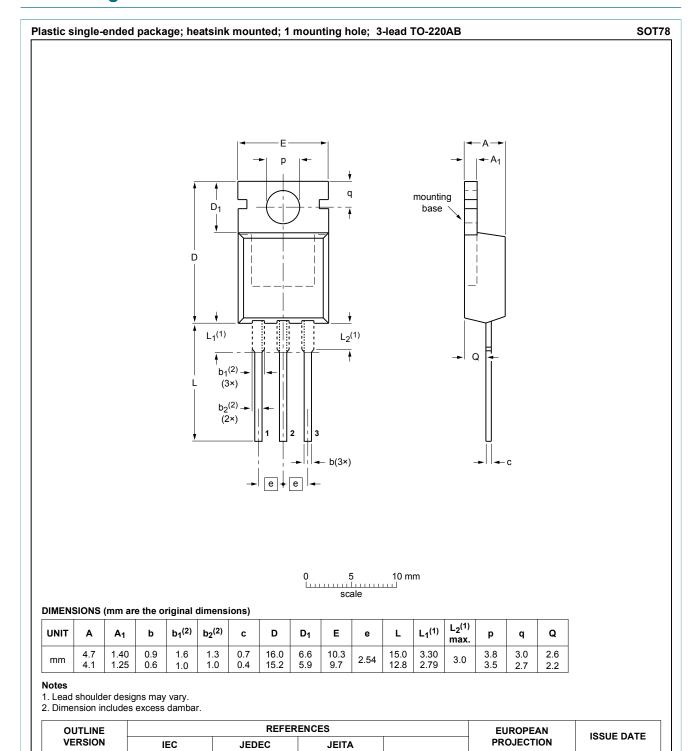


Fig. 9. Forward recovery definitions

**Dual ultrafast power diodes** 

## 10. Package outline



## SOT78 3-lead TO-220AB

Fig. 10. Package outline TO-220AB (SOT78)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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